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## Understanding **Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

## Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

### Details

Product Status	Active
Number of LABs/CLBs	160
Number of Logic Elements/Cells	1280
Total RAM Bits	65536
Number of I/O	107
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmx02-1200hc-4tg144i">https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmx02-1200hc-4tg144i</a>

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO2 family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks; these blocks are found in MachXO2-640/U and larger devices. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag “hard” control logic to minimize LUT usage.

The MachXO2 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO2 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks on MachXO2-640U, MachXO2-1200/U and larger devices. These blocks are located at the ends of the on-chip Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO2 devices provide commonly used hardened functions such as SPI controller, I<sup>2</sup>C controller and timer/counter. MachXO2-640/U and higher density devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I<sup>2</sup>C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO2 devices are available for operation from 3.3 V, 2.5 V and 1.2 V power supplies, providing easy integration into the overall system.

## **PFU Blocks**

The core of the MachXO2 device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.

## Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

### Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

### Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

### RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO2 devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO2 devices, please see TN1201, [Memory Usage Guide for MachXO2 Devices](#).

**Table 2-3. Number of Slices Required For Implementing Distributed RAM**

	SPR 16x4	PDPR 16x4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the  $t_{LOCK}$  parameter has been satisfied.

The MachXO2 also has a feature that allows the user to select between two different reference clock sources dynamically. This feature is implemented using the PLLREFCS primitive. The timing parameters for the PLL are shown in the [sysCLOCK PLL Timing](#) table.

The MachXO2 PLL contains a WISHBONE port feature that allows the PLL settings, including divider values, to be dynamically changed from the user logic. When using this feature the EFB block must also be instantiated in the design to allow access to the WISHBONE ports. Similar to the dynamic phase adjustment, when PLL settings are updated through the WISHBONE port the PLL may lose lock and not relock until the  $t_{LOCK}$  parameter has been satisfied. The timing parameters for the PLL are shown in the [sysCLOCK PLL Timing](#) table.

For more details on the PLL and the WISHBONE interface, see TN1199, [MachXO2 sysCLOCK PLL Design and Usage Guide](#).

**Figure 2-7. PLL Diagram**

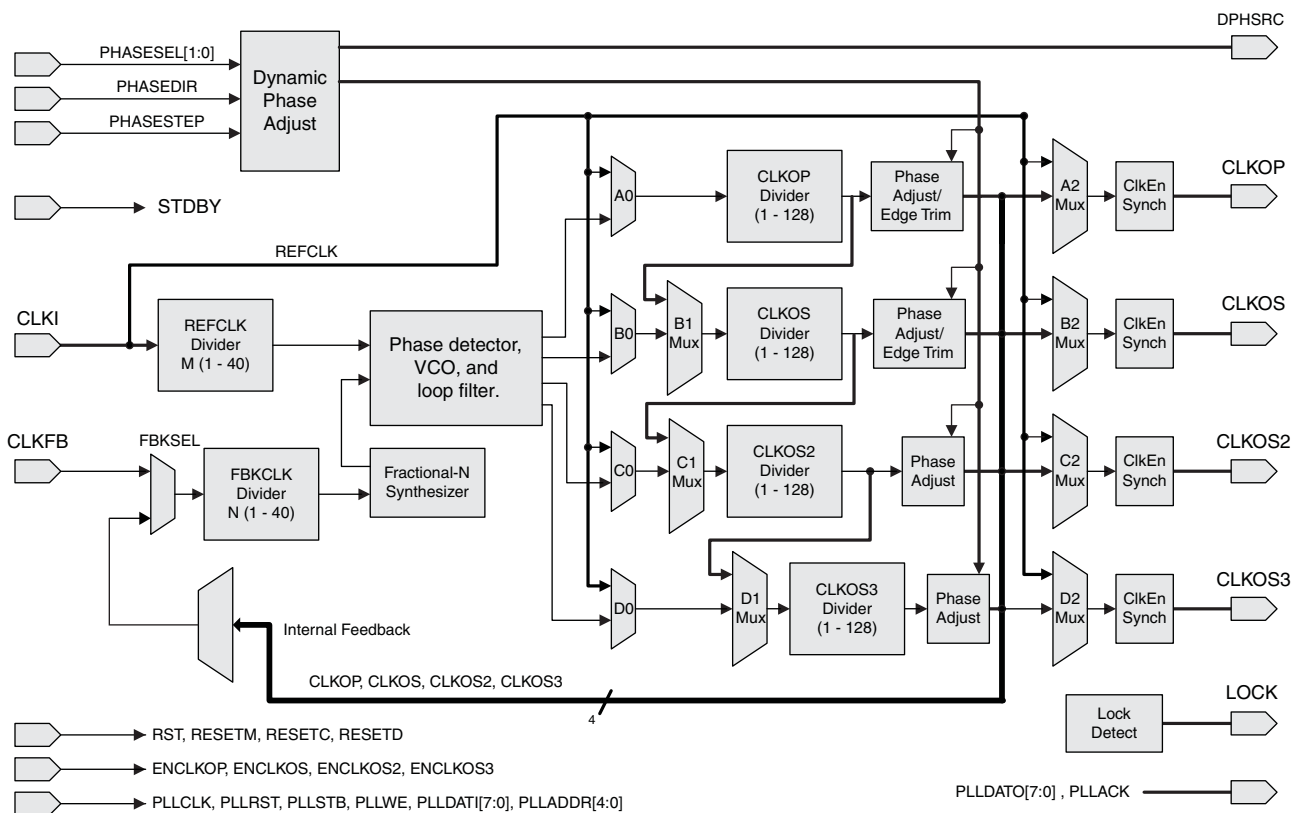


Table 2-4 provides signal descriptions of the PLL block.

**Table 2-4. PLL Signal Descriptions**

Port Name	I/O	Description
CLKI	I	Input clock to PLL
CLKFB	I	Feedback clock
PHASESEL[1:0]	I	Select which output is affected by Dynamic Phase adjustment ports
PHASEDIR	I	Dynamic Phase adjustment direction
PHASESTEP	I	Dynamic Phase step – toggle shifts VCO phase adjust by one step.

**Table 2-5. sysMEM Block Configurations**

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

### Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

### RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO2 devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

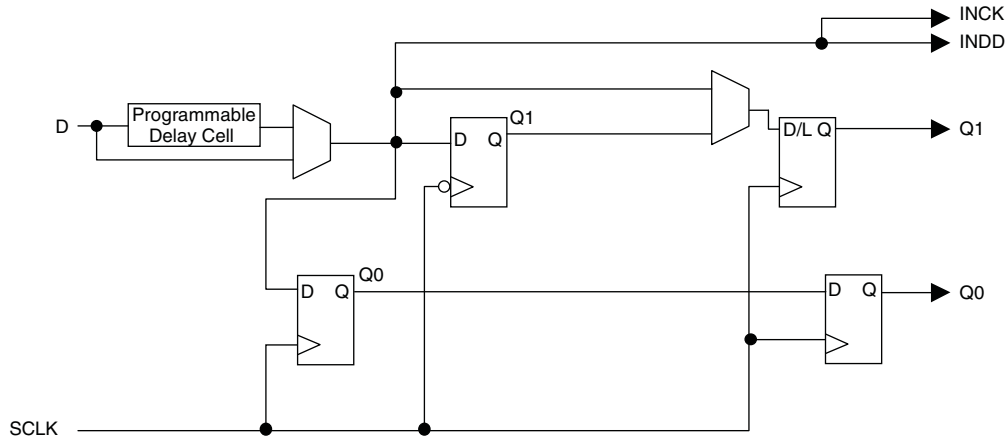
### Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

### Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

**Figure 2-12. MachXO2 Input Register Block Diagram (PIO on Left, Top and Bottom Edges)**



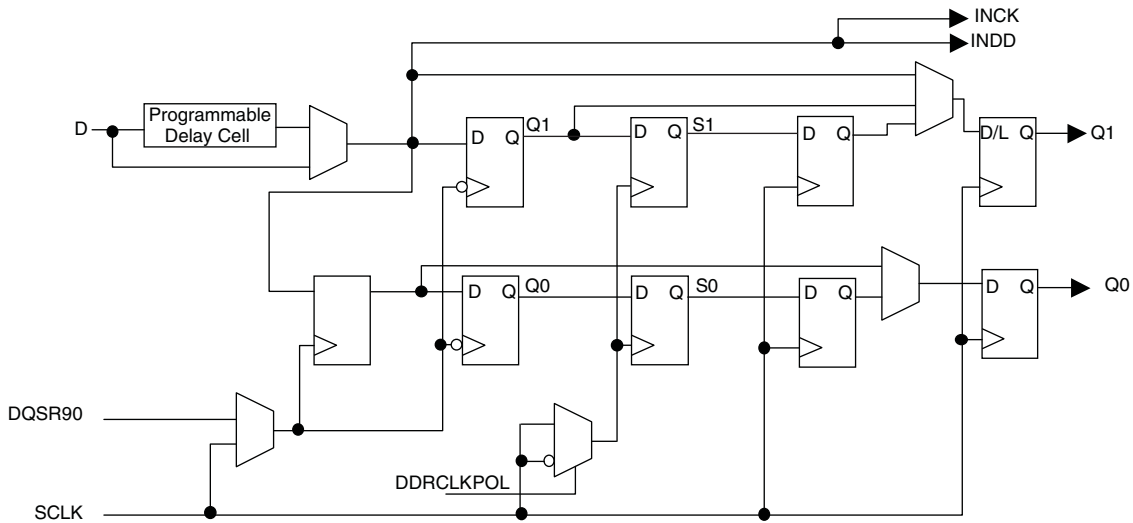
**Right Edge**

The input register block on the right edge is a superset of the same block on the top, bottom, and left edges. In addition to the modes described above, the input register block on the right edge also supports DDR memory mode.

In DDR memory mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (DQSR90) in the DDR Memory mode creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the DQS domain. The DQSR90 and DDRCLKPOL signals are generated in the DQS read-write block.

**Figure 2-13. MachXO2 Input Register Block Diagram (PIO on Right Edge)**



More information on the input gearbox is available in TN1203, [Implementing High-Speed Interfaces with MachXO2 Devices](#).

## Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDR4 (8:1) gearbox or as two ODDR2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

**Table 2-10. Output Gearbox Signal List**

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDR4(8:1): D[7:0]		
GDDR2(4:1)(IOL-A): D[3:0]		
GDDR2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-17 shows the output gearbox block diagram.

**Table 2-18. MachXO2 Power Saving Features Description**

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and referenced and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors V <sub>CC</sub> levels. In the event of unsafe V <sub>CC</sub> drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Referenced and differential I/O buffers (used to implement standards such as HSTL, SSTL and LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1198, [Power Estimation and Management for MachXO2 Devices](#).

## Power On Reset

MachXO2 devices have power-on reset circuitry to monitor V<sub>CCINT</sub> and V<sub>CCIO</sub> voltage levels during power-up and operation. At power-up, the POR circuitry monitors V<sub>CCINT</sub> and V<sub>CCIO0</sub> (controls configuration) voltage levels. It then triggers download from the on-chip configuration Flash memory after reaching the V<sub>PORUP</sub> level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For devices without voltage regulators (ZE and HE devices), V<sub>CCINT</sub> is the same as the V<sub>CC</sub> supply voltage. For devices with voltage regulators (HC devices), V<sub>CCINT</sub> is regulated from the V<sub>CC</sub> supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as Flash Download Time (t<sub>REFRESH</sub>) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration. Note that for HC devices, a separate POR circuit monitors external V<sub>CC</sub> voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V<sub>CCINT</sub> levels. If V<sub>CCINT</sub> drops below V<sub>PORDNBG</sub> level (with the bandgap circuitry switched on) or below V<sub>PORDNSRAM</sub> level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V<sub>CCINT</sub> and V<sub>CCIO</sub> voltage levels. V<sub>PORDNBG</sub> and V<sub>PORDNSRAM</sub> are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once a ZE or HE device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a minimal, low power POR circuit is still operational (this corresponds to the V<sub>PORDNSRAM</sub> reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V<sub>CC</sub> supply dropping below V<sub>CC</sub> (min) they should not shut down the bandgap or POR circuit.



When implementing background programming of the on-chip Flash, care must be taken for the operation of the PLL. For devices that have two PLLs (XO2-2000U, -4000 and -7000), the system must put the RPLL (Right-side PLL) in reset state during the background Flash programming. More detailed description can be found in TN1204, [MachXO2 Programming and Configuration Usage Guide](#).

### **Security and One-Time Programmable Mode (OTP)**

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO2 devices contain security bits that, when set, prevent the readback of the SRAM configuration and non-volatile Flash memory spaces. The device can be in one of two modes:

1. Unlocked – Readback of the SRAM configuration and non-volatile Flash memory spaces is allowed.
2. Permanently Locked – The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the Flash and SRAM OTP portions of the device. For more details, refer to TN1204, [MachXO2 Programming and Configuration Usage Guide](#).

### **Dual Boot**

MachXO2 devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the on-chip Flash. The golden image MUST reside in an external SPI Flash. For more details, refer to TN1204, [MachXO2 Programming and Configuration Usage Guide](#).

### **Soft Error Detection**

The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1206, [MachXO2 Soft Error Detection Usage Guide](#).

### **TracelD**

Each MachXO2 device contains a unique (per device), TracelD that can be used for tracking purposes or for IP security applications. The TracelD is 64 bits long. Eight out of 64 bits are user-programmable, the remaining 56 bits are factory-programmed. The TracelD is accessible through the EFB WISHBONE interface and can also be accessed through the SPI, I<sup>2</sup>C, or JTAG interfaces.

### **Density Shifting**

The MachXO2 family has been designed to enable density migration within the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case. When migrating from lower to higher density or higher to lower density, ensure to review all the power supplies and NC pins of the chosen devices. For more details refer to the [MachXO2 migration files](#).



# MachXO2 Family Data Sheet

## DC and Switching Characteristics

March 2017

Data Sheet DS1035

### Absolute Maximum Ratings<sup>1, 2, 3</sup>

	MachXO2 ZE/HE (1.2 V)	MachXO2 HC (2.5 V / 3.3 V)
Supply Voltage $V_{CC}$ . . . . .	-0.5 V to 1.32 V . . . . .	-0.5 V to 3.75 V . . . . .
Output Supply Voltage $V_{CCIO}$ . . . . .	-0.5 V to 3.75 V . . . . .	-0.5 V to 3.75 V . . . . .
I/O Tri-state Voltage Applied <sup>4, 5</sup> . . . . .	-0.5 V to 3.75 V . . . . .	-0.5 V to 3.75 V . . . . .
Dedicated Input Voltage Applied <sup>4</sup> . . . . .	-0.5 V to 3.75 V . . . . .	-0.5 V to 3.75 V . . . . .
Storage Temperature (Ambient) . . . . .	-55 °C to 125 °C . . . . .	-55 °C to 125 °C . . . . .
Junction Temperature ( $T_J$ ) . . . . .	-40 °C to 125 °C . . . . .	-40 °C to 125 °C . . . . .

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice [Thermal Management](#) document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of -2 V to ( $V_{IHMAX} + 2$ ) volts is permitted for a duration of <20 ns.
5. The dual function I<sup>2</sup>C pins SCL and SDA are limited to -0.25 V to 3.75 V or to -0.3 V with a duration of <20 ns.

### Recommended Operating Conditions<sup>1</sup>

Symbol	Parameter	Min.	Max.	Units
$V_{CC}^1$	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
	Core Supply Voltage for 2.5 V / 3.3 V Devices	2.375	3.6	V
$V_{CCIO}^{1, 2, 3}$	I/O Driver Supply Voltage	1.14	3.6	V
$t_{JCOM}$	Junction Temperature Commercial Operation	0	85	°C
$t_{JIND}$	Junction Temperature Industrial Operation	-40	100	°C

1. Like power supplies must be tied together. For example, if  $V_{CCIO}$  and  $V_{CC}$  are both the same voltage, they must also be the same supply.
2. See recommended voltages by I/O standard in subsequent table.
3.  $V_{CCIO}$  pins of unused I/O banks should be connected to the  $V_{CC}$  power supply on boards.

### Power Supply Ramp Rates<sup>1</sup>

Symbol	Parameter	Min.	Typ.	Max.	Units
$t_{RAMP}$	Power supply ramp rates for all power supplies.	0.01	—	100	V/ms

1. Assumes monotonic ramp rates.

**Programming and Erase Flash Supply Current – ZE Devices<sup>1, 2, 3, 4</sup>**

Symbol	Parameter	Device	Typ. <sup>5</sup>	Units
I <sub>CC</sub>	Core Power Supply	LCMXO2-256ZE	13	mA
		LCMXO2-640ZE	14	mA
		LCMXO2-1200ZE	15	mA
		LCMXO2-2000ZE	17	mA
		LCMXO2-4000ZE	18	mA
		LCMXO2-7000ZE	20	mA
I <sub>CCIO</sub>	Bank Power Supply <sup>6</sup>	All devices	0	mA

1. For further information on supply current, please refer to TN1198, [Power Estimation and Management for MachXO2 Devices](#).

2. Assumes all inputs are held at V<sub>CCIO</sub> or GND and all outputs are tri-stated.

3. Typical user pattern.

4. JTAG programming is at 25 MHz.

5. T<sub>J</sub> = 25 °C, power supplies at nominal voltage.

6. Per bank. V<sub>CCIO</sub> = 2.5 V. Does not include pull-up/pull-down.

**sysIO Single-Ended DC Electrical Characteristics<sup>1, 2</sup>**

Input/Output Standard	$V_{IL}$		$V_{IH}$		$V_{OL}$ Max. (V)	$V_{OH}$ Min. (V)	$I_{OL}$ Max. <sup>4</sup> (mA)	$I_{OH}$ Max. <sup>4</sup> (mA)
	Min. (V) <sup>3</sup>	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
							24	-24
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
LVCMOS 1.8	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.5	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.2	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-2
							8	-6
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
PCI	-0.3	$0.3V_{CCIO}$	$0.5V_{CCIO}$	3.6	$0.1V_{CCIO}$	$0.9V_{CCIO}$	1.5	-0.5
SSTL25 Class I	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.54	$V_{CCIO} - 0.62$	8	8
SSTL25 Class II	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	NA	NA	NA	NA
SSTL18 Class I	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
SSTL18 Class II	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	NA	NA	NA	NA
HSTL18 Class I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
HSTL18 Class II	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS25R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain

## Typical Building Block Function Performance – HC/HE Devices<sup>1</sup>

### Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	-6 Timing	Units
<b>Basic Functions</b>		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

### Register-to-Register Performance

Function	-6 Timing	Units
<b>Basic Functions</b>		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
<b>Embedded Memory Functions</b>		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
<b>Distributed Memory Functions</b>		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

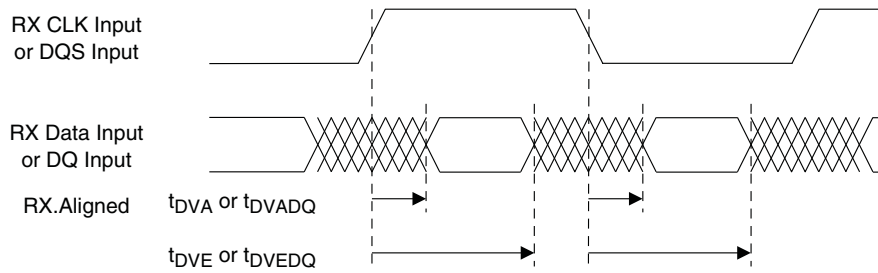
1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

Parameter	Description	Device	-3		-2		-1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
<b>Generic DDRX2 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR2_TX.ECLK.Centered<sup>9,12</sup></b>									
t <sub>DVB</sub>	Output Data Valid Before CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	1.445	—	1.760	—	2.140	—	ns
t <sub>DVA</sub>	Output Data Valid After CLK Output		1.445	—	1.760	—	2.140	—	ns
f <sub>DATA</sub>	DDR2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f <sub>DDR2</sub>	DDR2 ECLK Frequency (minimum limited by PLL)		—	140	—	117	—	97	MHz
f <sub>SCLK</sub>	SCLK Frequency		—	70	—	59	—	49	MHz
<b>Generic DDRX4 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDR4_TX.ECLK.Aligned<sup>9,12</sup></b>									
t <sub>DIA</sub>	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t <sub>DIB</sub>	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f <sub>DATA</sub>	DDR4 Serial Output Data Speed		—	420	—	352	—	292	Mbps
f <sub>DDR4</sub>	DDR4 ECLK Frequency		—	210	—	176	—	146	MHz
f <sub>SCLK</sub>	SCLK Frequency		—	53	—	44	—	37	MHz
<b>Generic DDRX4 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR4_TX.ECLK.Centered<sup>9,12</sup></b>									
t <sub>DVB</sub>	Output Data Valid Before CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	0.873	—	1.067	—	1.319	—	ns
t <sub>DVA</sub>	Output Data Valid After CLK Output		0.873	—	1.067	—	1.319	—	ns
f <sub>DATA</sub>	DDR4 Serial Output Data Speed		—	420	—	352	—	292	Mbps
f <sub>DDR4</sub>	DDR4 ECLK Frequency (minimum limited by PLL)		—	210	—	176	—	146	MHz
f <sub>SCLK</sub>	SCLK Frequency		—	53	—	44	—	37	MHz
<b>7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1<sup>9,12</sup></b>									
t <sub>DIB</sub>	Output Data Invalid Before CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only.	—	0.240	—	0.270	—	0.300	ns
t <sub>DIA</sub>	Output Data Invalid After CLK Output		—	0.240	—	0.270	—	0.300	ns
f <sub>DATA</sub>	DDR71 Serial Output Data Speed		—	420	—	352	—	292	Mbps
f <sub>DDR71</sub>	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f <sub>CLKOUT</sub>	7:1 Output Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz

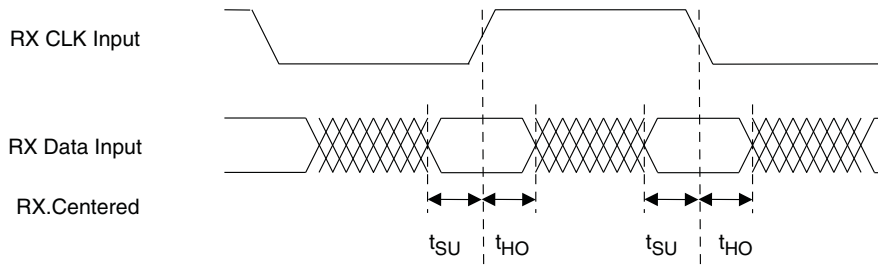
Parameter	Description	Device	-3		-2		-1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
<b>LPDDR<sup>9, 12</sup></b>									
t <sub>DVADQ</sub>	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only. <sup>13</sup>	—	0.349	—	0.381	—	0.396	UI
t <sub>DVEDQ</sub>	Input Data Hold After DQS Input		0.665	—	0.630	—	0.613	—	UI
t <sub>DQVBS</sub>	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t <sub>DQVAS</sub>	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f <sub>DATA</sub>	MEM LPDDR Serial Data Speed		—	120	—	110	—	96	Mbps
f <sub>SCLK</sub>	SCLK Frequency		—	60	—	55	—	48	MHz
f <sub>LPDDR</sub>	LPDDR Data Transfer Rate		0	120	0	110	0	96	Mbps
<b>DDR<sup>9, 12</sup></b>									
t <sub>DVADQ</sub>	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only. <sup>13</sup>	—	0.347	—	0.374	—	0.393	UI
t <sub>DVEDQ</sub>	Input Data Hold After DQS Input		0.665	—	0.637	—	0.616	—	UI
t <sub>DQVBS</sub>	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t <sub>DQVAS</sub>	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f <sub>DATA</sub>	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f <sub>SCLK</sub>	SCLK Frequency		—	70	—	58	—	49	MHz
f <sub>MEM_DDR</sub>	MEM DDR Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps
<b>DDR2<sup>9, 12</sup></b>									
t <sub>DVADQ</sub>	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only. <sup>13</sup>	—	0.372	—	0.394	—	0.410	UI
t <sub>DVEDQ</sub>	Input Data Hold After DQS Input		0.690	—	0.658	—	0.618	—	UI
t <sub>DQVBS</sub>	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t <sub>DQVAS</sub>	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f <sub>DATA</sub>	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f <sub>SCLK</sub>	SCLK Frequency		—	70	—	58	—	49	MHz
f <sub>MEM_DDR2</sub>	MEM DDR2 Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0 pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode  $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03 \text{ ns})/2$ .
7. The t<sub>SU\_DEL</sub> and t<sub>H\_DEL</sub> values use the SCLK\_ZERHOLD default step size. Each step is 167 ps (-3), 182 ps (-2), 195 ps (-1).
8. This number for general purpose usage. Duty cycle tolerance is +/-10%.
9. Duty cycle is +/- 5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32-Pin QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

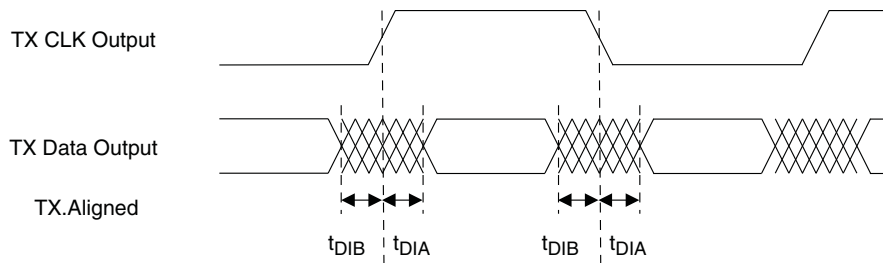
**Figure 3-5. Receiver RX.CLK.Aligned and MEM DDR Input Waveforms**



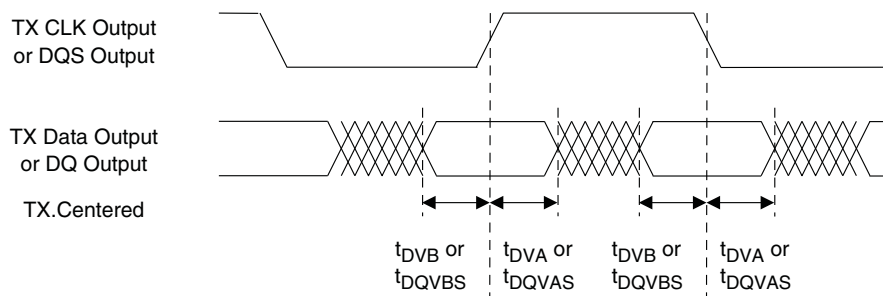
**Figure 3-6. Receiver RX.CLK.Centered Waveforms**



**Figure 3-7. Transmitter TX.CLK.Aligned Waveforms**



**Figure 3-8. Transmitter TX.CLK.Centered and MEM DDR Output Waveforms**





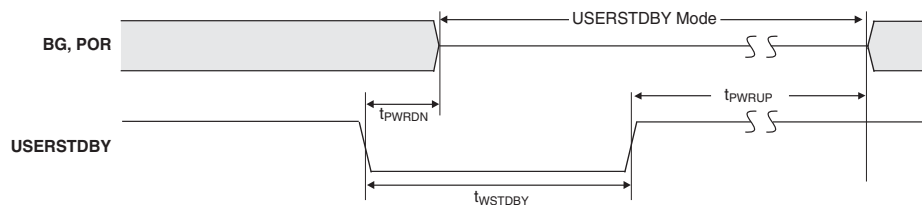
### MachXO2 Oscillator Output Frequency

Symbol	Parameter	Min.	Typ.	Max	Units
f <sub>MAX</sub>	Oscillator Output Frequency (Commercial Grade Devices, 0 to 85°C)	125.685	133	140.315	MHz
	Oscillator Output Frequency (Industrial Grade Devices, -40 °C to 100 °C)	124.355	133	141.645	MHz
t <sub>DT</sub>	Output Clock Duty Cycle	43	50	57	%
t <sub>OPJIT</sub> <sup>1</sup>	Output Clock Period Jitter	0.01	0.012	0.02	UIPP
t <sub>STABLEOSC</sub>	STDBY Low to Oscillator Stable	0.01	0.05	0.1	µs

1. Output Clock Period Jitter specified at 133 MHz. The values for lower frequencies will be smaller UIPP. The typical value for 133 MHz is 95 ps and for 2.08 MHz the typical value is 1.54 ns.

### MachXO2 Standby Mode Timing – HC/HE Devices

Symbol	Parameter	Device	Min.	Typ.	Max	Units
t <sub>PWRDN</sub>	USERSTDBY High to Stop	All	—	—	9	ns
t <sub>PWRUP</sub>	USERSTDBY Low to Power Up	LCMXO2-256		—		µs
		LCMXO2-640		—		µs
		LCMXO2-640U		—		µs
		LCMXO2-1200	20	—	50	µs
		LCMXO2-1200U		—		µs
		LCMXO2-2000		—		µs
		LCMXO2-2000U		—		µs
		LCMXO2-4000		—		µs
LCMXO2-7000		—		µs		
t <sub>WSTDBY</sub>	USERSTDBY Pulse Width	All	18	—	—	ns



### MachXO2 Standby Mode Timing – ZE Devices

Symbol	Parameter	Device	Min.	Typ.	Max	Units
t <sub>PWRDN</sub>	USERSTDBY High to Stop	All	—	—	13	ns
t <sub>PWRUP</sub>	USERSTDBY Low to Power Up	LCMXO2-256		—		µs
		LCMXO2-640		—		µs
		LCMXO2-1200	20	—	50	µs
		LCMXO2-2000		—		µs
		LCMXO2-4000		—		µs
		LCMXO2-7000		—		µs
t <sub>WSTDBY</sub>	USERSTDBY Pulse Width	All	19	—	—	ns
t <sub>BNDGAPSTBL</sub>	USERSTDBY High to Bandgap Stable	All	—	—	15	ns

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000ZE-1UWG49ITR <sup>1</sup>	2112	1.2 V	-1	Halogen-Free WLCSP	49	IND
LCMXO2-2000ZE-1UWG49ITR50 <sup>3</sup>	2112	1.2 V	-1	Halogen-Free WLCSP	49	IND
LCMXO2-2000ZE-1UWG49ITR1K <sup>2</sup>	2112	1.2 V	-1	Halogen-Free WLCSP	49	IND
LCMXO2-2000ZE-1TG100I	2112	1.2 V	-1	Halogen-Free TQFP	100	IND
LCMXO2-2000ZE-2TG100I	2112	1.2 V	-2	Halogen-Free TQFP	100	IND
LCMXO2-2000ZE-3TG100I	2112	1.2 V	-3	Halogen-Free TQFP	100	IND
LCMXO2-2000ZE-1MG132I	2112	1.2 V	-1	Halogen-Free csBGA	132	IND
LCMXO2-2000ZE-2MG132I	2112	1.2 V	-2	Halogen-Free csBGA	132	IND
LCMXO2-2000ZE-3MG132I	2112	1.2 V	-3	Halogen-Free csBGA	132	IND
LCMXO2-2000ZE-1TG144I	2112	1.2 V	-1	Halogen-Free TQFP	144	IND
LCMXO2-2000ZE-2TG144I	2112	1.2 V	-2	Halogen-Free TQFP	144	IND
LCMXO2-2000ZE-3TG144I	2112	1.2 V	-3	Halogen-Free TQFP	144	IND
LCMXO2-2000ZE-1BG256I	2112	1.2 V	-1	Halogen-Free caBGA	256	IND
LCMXO2-2000ZE-2BG256I	2112	1.2 V	-2	Halogen-Free caBGA	256	IND
LCMXO2-2000ZE-3BG256I	2112	1.2 V	-3	Halogen-Free caBGA	256	IND
LCMXO2-2000ZE-1FTG256I	2112	1.2 V	-1	Halogen-Free ftBGA	256	IND
LCMXO2-2000ZE-2FTG256I	2112	1.2 V	-2	Halogen-Free ftBGA	256	IND
LCMXO2-2000ZE-3FTG256I	2112	1.2 V	-3	Halogen-Free ftBGA	256	IND

1. This part number has a tape and reel quantity of 5,000 units with a minimum order quantity of 10,000 units. Order quantities must be in increments of 5,000 units. For example, a 10,000 unit order will be shipped in two reels with one reel containing 5,000 units and the other reel with less than 5,000 units (depending on test yields). Unserviced backlog will be canceled.
2. This part number has a tape and reel quantity of 1,000 units with a minimum order quantity of 1,000. Order quantities must be in increments of 1,000 units. For example, a 5,000 unit order will be shipped as 5 reels of 1000 units each.
3. This part number has a tape and reel quantity of 50 units with a minimum order quantity of 50. Order quantities must be in increments of 50 units. For example, a 1,000 unit order will be shipped as 20 reels of 50 units each.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000ZE-1QN84I	4320	1.2 V	-1	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-2QN84I	4320	1.2 V	-2	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-3QN84I	4320	1.2 V	-3	Halogen-Free QFN	84	IND
LCMXO2-4000ZE-1MG132I	4320	1.2 V	-1	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-2MG132I	4320	1.2 V	-2	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-3MG132I	4320	1.2 V	-3	Halogen-Free csBGA	132	IND
LCMXO2-4000ZE-1TG144I	4320	1.2 V	-1	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-2TG144I	4320	1.2 V	-2	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-3TG144I	4320	1.2 V	-3	Halogen-Free TQFP	144	IND
LCMXO2-4000ZE-1BG256I	4320	1.2 V	-1	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-2BG256I	4320	1.2 V	-2	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-3BG256I	4320	1.2 V	-3	Halogen-Free caBGA	256	IND
LCMXO2-4000ZE-1FTG256I	4320	1.2 V	-1	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-2FTG256I	4320	1.2 V	-2	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-3FTG256I	4320	1.2 V	-3	Halogen-Free ftBGA	256	IND
LCMXO2-4000ZE-1BG332I	4320	1.2 V	-1	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-2BG332I	4320	1.2 V	-2	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-3BG332I	4320	1.2 V	-3	Halogen-Free caBGA	332	IND
LCMXO2-4000ZE-1FG484I	4320	1.2 V	-1	Halogen-Free fpBGA	484	IND
LCMXO2-4000ZE-2FG484I	4320	1.2 V	-2	Halogen-Free fpBGA	484	IND
LCMXO2-4000ZE-3FG484I	4320	1.2 V	-3	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000ZE-1TG144I	6864	1.2 V	-1	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-2TG144I	6864	1.2 V	-2	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-3TG144I	6864	1.2 V	-3	Halogen-Free TQFP	144	IND
LCMXO2-7000ZE-1BG256I	6864	1.2 V	-1	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-2BG256I	6864	1.2 V	-2	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-3BG256I	6864	1.2 V	-3	Halogen-Free caBGA	256	IND
LCMXO2-7000ZE-1FTG256I	6864	1.2 V	-1	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-2FTG256I	6864	1.2 V	-2	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-3FTG256I	6864	1.2 V	-3	Halogen-Free ftBGA	256	IND
LCMXO2-7000ZE-1BG332I	6864	1.2 V	-1	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-2BG332I	6864	1.2 V	-2	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-3BG332I	6864	1.2 V	-3	Halogen-Free caBGA	332	IND
LCMXO2-7000ZE-1FG484I	6864	1.2 V	-1	Halogen-Free fpBGA	484	IND
LCMXO2-7000ZE-2FG484I	6864	1.2 V	-2	Halogen-Free fpBGA	484	IND
LCMXO2-7000ZE-3FG484I	6864	1.2 V	-3	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-4MG132I	4320	1.2 V	-4	Halogen-Free csBGA	132	IND
LCMXO2-4000HE-5MG132I	4320	1.2 V	-5	Halogen-Free csBGA	132	IND
LCMXO2-4000HE-6MG132I	4320	1.2 V	-6	Halogen-Free csBGA	132	IND
LCMXO2-4000HE-4TG144I	4320	1.2 V	-4	Halogen-Free TQFP	144	IND
LCMXO2-4000HE-5TG144I	4320	1.2 V	-5	Halogen-Free TQFP	144	IND
LCMXO2-4000HE-6TG144I	4320	1.2 V	-6	Halogen-Free TQFP	144	IND
LCMXO2-4000HE-4MG184I	4320	1.2 V	-4	Halogen-Free csBGA	184	IND
LCMXO2-4000HE-5MG184I	4320	1.2 V	-5	Halogen-Free csBGA	184	IND
LCMXO2-4000HE-6MG184I	4320	1.2 V	-6	Halogen-Free csBGA	184	IND
LCMXO2-4000HE-4BG256I	4320	1.2 V	-4	Halogen-Free caBGA	256	IND
LCMXO2-4000HE-5BG256I	4320	1.2 V	-5	Halogen-Free caBGA	256	IND
LCMXO2-4000HE-6BG256I	4320	1.2 V	-6	Halogen-Free caBGA	256	IND
LCMXO2-4000HE-4FTG256I	4320	1.2 V	-4	Halogen-Free ftBGA	256	IND
LCMXO2-4000HE-5FTG256I	4320	1.2 V	-5	Halogen-Free ftBGA	256	IND
LCMXO2-4000HE-6FTG256I	4320	1.2 V	-6	Halogen-Free ftBGA	256	IND
LCMXO2-4000HE-4BG332I	4320	1.2 V	-4	Halogen-Free caBGA	332	IND
LCMXO2-4000HE-5BG332I	4320	1.2 V	-5	Halogen-Free caBGA	332	IND
LCMXO2-4000HE-6BG332I	4320	1.2 V	-6	Halogen-Free caBGA	332	IND
LCMXO2-4000HE-4FG484I	4320	1.2 V	-4	Halogen-Free fpBGA	484	IND
LCMXO2-4000HE-5FG484I	4320	1.2 V	-5	Halogen-Free fpBGA	484	IND
LCMXO2-4000HE-6FG484I	4320	1.2 V	-6	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HE-4TG144I	6864	1.2 V	-4	Halogen-Free TQFP	144	IND
LCMXO2-7000HE-5TG144I	6864	1.2 V	-5	Halogen-Free TQFP	144	IND
LCMXO2-7000HE-6TG144I	6864	1.2 V	-6	Halogen-Free TQFP	144	IND
LCMXO2-7000HE-4BG256I	6864	1.2 V	-4	Halogen-Free caBGA	256	IND
LCMXO2-7000HE-5BG256I	6864	1.2 V	-5	Halogen-Free caBGA	256	IND
LCMXO2-7000HE-6BG256I	6864	1.2 V	-6	Halogen-Free caBGA	256	IND
LCMXO2-7000HE-4FTG256I	6864	1.2 V	-4	Halogen-Free ftBGA	256	IND
LCMXO2-7000HE-5FTG256I	6864	1.2 V	-5	Halogen-Free ftBGA	256	IND
LCMXO2-7000HE-6FTG256I	6864	1.2 V	-6	Halogen-Free ftBGA	256	IND
LCMXO2-7000HE-4BG332I	6864	1.2 V	-4	Halogen-Free caBGA	332	IND
LCMXO2-7000HE-5BG332I	6864	1.2 V	-5	Halogen-Free caBGA	332	IND
LCMXO2-7000HE-6BG332I	6864	1.2 V	-6	Halogen-Free caBGA	332	IND
LCMXO2-7000HE-4FG484I	6864	1.2 V	-4	Halogen-Free fpBGA	484	IND
LCMXO2-7000HE-5FG484I	6864	1.2 V	-5	Halogen-Free fpBGA	484	IND
LCMXO2-7000HE-6FG484I	6864	1.2 V	-6	Halogen-Free fpBGA	484	IND

## R1 Device Specifications

The LCMXO2-1200ZE/HC “R1” devices have the same specifications as their Standard (non-R1) counterparts except as listed below. For more details on the R1 to Standard migration refer to AN8086, [Designing for Migration from MachXO2-1200-R1 to Standard Non-R1\) Devices](#).

- The User Flash Memory (UFM) cannot be programmed through the internal WISHBONE interface. It can still be programmed through the JTAG/SPI/I<sup>2</sup>C ports.
- The on-chip differential input termination resistor value is higher than intended. It is approximately 200Ω as opposed to the intended 100Ω. It is recommended to use external termination resistors for differential inputs. The on-chip termination resistors can be disabled through Lattice design software.
- Soft Error Detection logic may not produce the correct result when it is run for the first time after configuration. To use this feature, discard the result from the first operation. Subsequent operations will produce the correct result.
- Under certain conditions, I<sub>IH</sub> exceeds data sheet specifications. The following table provides more details:

Condition	Clamp	Pad Rising I <sub>IH</sub> Max.	Pad Falling I <sub>IH</sub> Min.	Steady State Pad High I <sub>IH</sub>	Steady State Pad Low I <sub>IL</sub>
VPAD > VCCIO	OFF	1 mA	-1 mA	1 mA	10 μA
VPAD = VCCIO	ON	10 μA	-10 μA	10 μA	10 μA
VPAD = VCCIO	OFF	1 mA	-1 mA	1 mA	10 μA
VPAD < VCCIO	OFF	10 μA	-10 μA	10 μA	10 μA

- The user SPI interface does not operate correctly in some situations. During master read access and slave write access, the last byte received does not generate the RRDY interrupt.
- In GDDR2, GDDR4 and GDDR71 modes, ECLKSYNC may have a glitch in the output under certain conditions, leading to possible loss of synchronization.
- When using the hard I<sup>2</sup>C IP core, the I<sup>2</sup>C status registers I2C\_1\_SR and I2C\_2\_SR may not update correctly.
- PLL Lock signal will glitch high when coming out of standby. This glitch lasts for about 10 μsec before returning low.
- Dual boot only available on HC devices, requires tying VCC and VCCIO2 to the same 3.3 V or 2.5 V supply.